Gate resistor installed
Dual N-channel MOSFET

KFC4B22670L
Data Sheet

For additional information or question, please contact Nuvoton Technology Corporation Japan.
www.nuvoton.co.jp

1. GENERAL DESCRIPTION

Gate resistor installed Dual N-channel MOSFET
For lithium-ion secondary battery protection circuits

2. FEATURES

- Source-source ON resistance: Rss(on) typ. = 38 mΩ (VGS = 3.7 V)
- CSP (Chip Size Package)
- Halogen-free / RoHS compliant (EU RoHS / UL-94 V-0 / MSL: Level 1)

3. MARKING SYMBOL: 6E

4. PACKAGING

Embossed type (Thermo-compression sealing): 20,000 pcs / reel (standard)

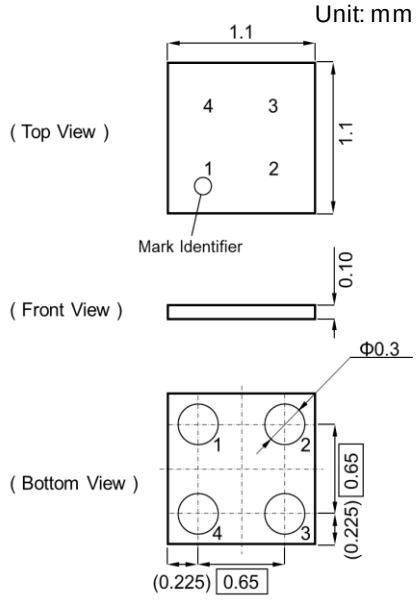
5. ABSOLUTE MAXIMUM RATINGS Ta = 25 °C

Parameter		Symbol	Rating	Unit
Source-source Voltage		VSS	20	V
Gate-source Voltage		VGS	±12	V
Source Current	DC	IS1 *1	2.9	A
		IS2 *2	4.6	
		IS3 *3	6.1	
	Pulsed *4	ISp	29	
Total Power Dissipation	DC	PD1 *1	0.42	W
		PD2 *2	1.1	
		PD3 *3	1.9	
Channel Temperature		Tch	150	°C
Storage Temperature Range		Tstg	-55 to +150	°C

6. THERMAL CHARACTERISTICS Ta = 25 °C

Parameter	Symbol	Rating	Unit
Thermal Resistance (ch-a)	Rth1 *1	292	°C / W
	Rth2 *2	113	
	Rth3 *3	66	

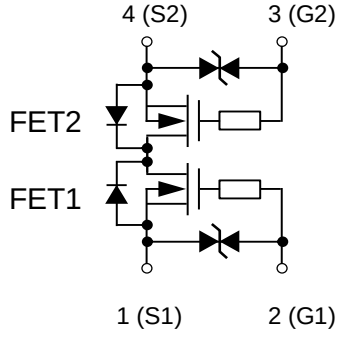
Note *1 Mounted on FR4 board (25.4 mm x 25.4 mm x t1.0 mm),
FR4 board partially covered with copper pad (18 mm^2 area, 36 μm thickness).
*2 Mounted on FR4 board (25.4 mm x 25.4 mm x t1.0 mm).
FR4 board fully covered with copper pad (608 mm^2 area, 36 μm thickness).
*3 Mounted on Ceramic board (70 mm x 70 mm x t1.0 mm).
*4 t = 10 μs, Duty Cycle ≤ 1 %



1. Source1 (FET1) 2. Gate1 (FET1)
3. Gate2 (FET2) 4. Source2 (FET2)

Package	MLGA004-W-1111-RA
JEITA	-
Code	-

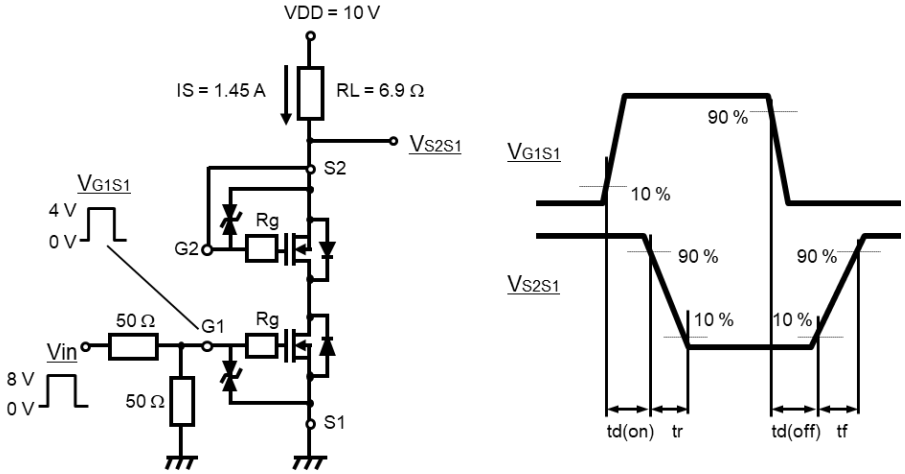
Equivalent circuit



7. ELECTRICAL CHARACTERISTICS Ta = 25 °C ± 3 °C

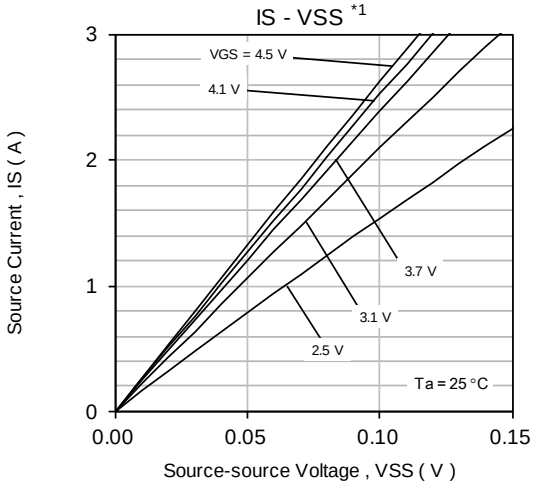
Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Source-source Breakdown Voltage	VSSS	IS = 1 mA, VGS = 0 V	20			V
Zero Gate Voltage Source Current	ISSS	VSS = 20 V, VGS = 0 V			1.0	μA
Gate-Source Leakage Current	IGSS1	VGS = ±8 V, VSS = 0 V			±1.0	μA
	IGSS2	VGS = ±3.8 V, VSS = 0 V			±0.1	
Gate-source Threshold Voltage	Vth	IS = 0.1 mA, VSS = 10 V	0.35	0.90	1.40	V
Source-source On-state Resistance	RSS(on)1	IS = 1.45 A, VGS = 4.5 V	29.0	35.0	45.0	mΩ
	RSS(on)2	IS = 1.45 A, VGS = 4.1 V	31.0	37.0	48.0	
	RSS(on)3	IS = 1.45 A, VGS = 4.0 V	31.0	37.0	48.0	
	RSS(on)4	IS = 1.45 A, VGS = 3.8 V	31.0	37.5	49.0	
	RSS(on)5	IS = 1.45 A, VGS = 3.7 V	31.5	38.0	50.0	
	RSS(on)6	IS = 1.45 A, VGS = 3.1 V	33.0	42.0	57.0	
	RSS(on)7	IS = 1.45 A, VGS = 2.5 V	34.0	64.0	100	
Body Diode Forward Voltage	VF(s-s)	IF = 1.45 A, VGS = 0 V		0.8	1.2	V
Input Capacitance *1	Ciss	VSS = 10 V, VGS = 0 V, f = 1 kHz		440		pF
Output Capacitance *1	Coss			82		
Reverse Transfer Capacitance *1	Crss			68		
Turn-on Delay Time *1,*2	td(on)	VDD = 10 V, VGS = 0 to 4 V IS = 1.45 A		0.12		μs
Rise Time *1,*2	tr			0.26		
Turn-off Delay Time *1,*2	td(off)	VDD = 10 V, VGS = 4 to 0 V IS = 1.45 A		0.54		μs
Fall Time *1,*2	tf			0.39		
Total Gate Charge *1	Qg	VDD = 10 V VGS = 0 to 4 V IS = 2.9 A		4.5		nC
Gate-source Charge *1	Qgs			1.1		
Gate-drain Charge *1	Qgd			1.2		

Note Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 Measuring methods for transistors.
*1 Guaranteed by design, not subject to production testing
*2 Measurement circuit for Turn-on Delay Time / Rise Time / Turn-off Delay Time / Fall Time

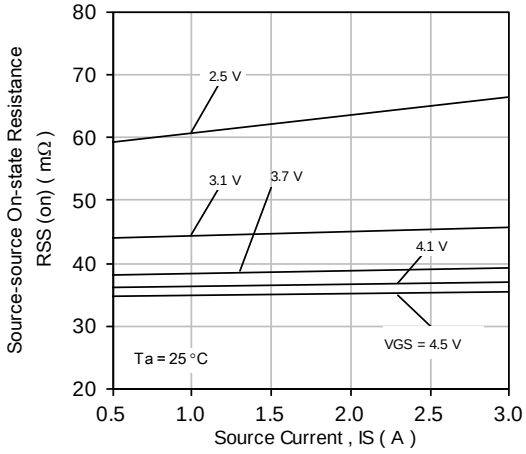


8. TECHNICAL DATA (Reference)

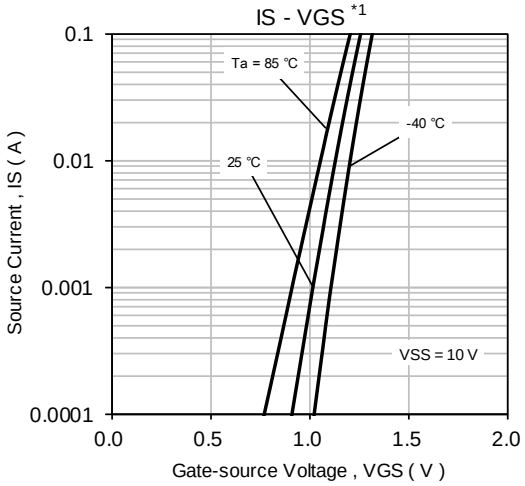
IS - VSS *1



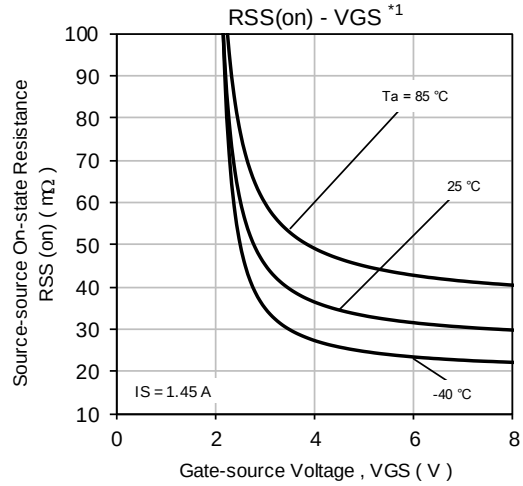
RSS(on) - IS *1



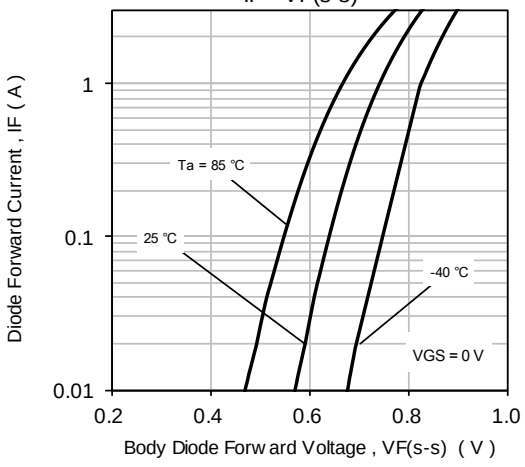
IS - VGS *1



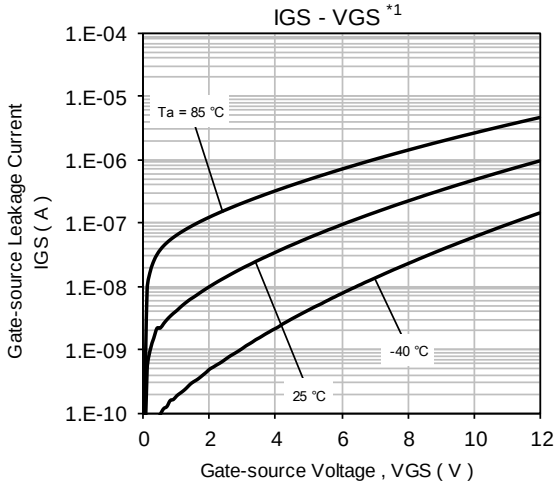
RSS(on) - VGS *1



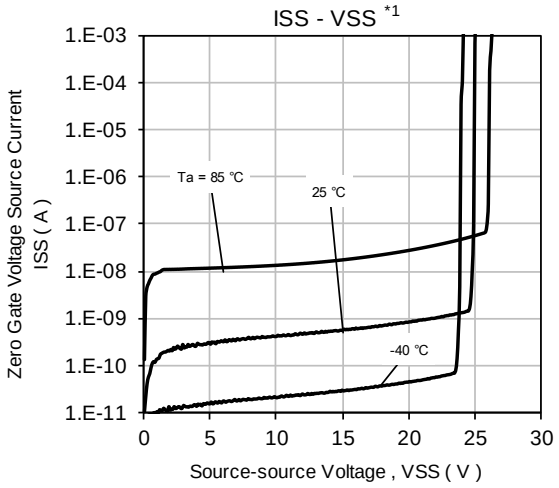
IF - VF(s-s) *1

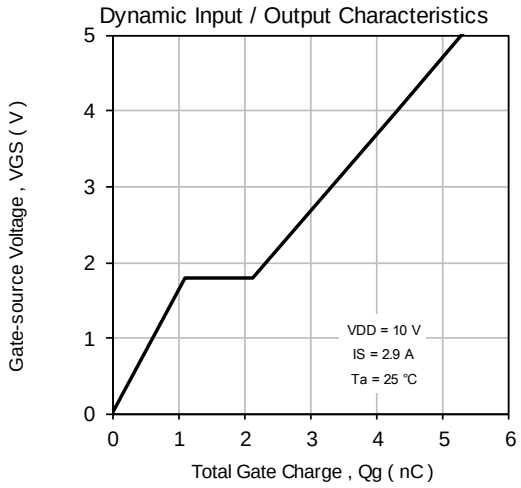


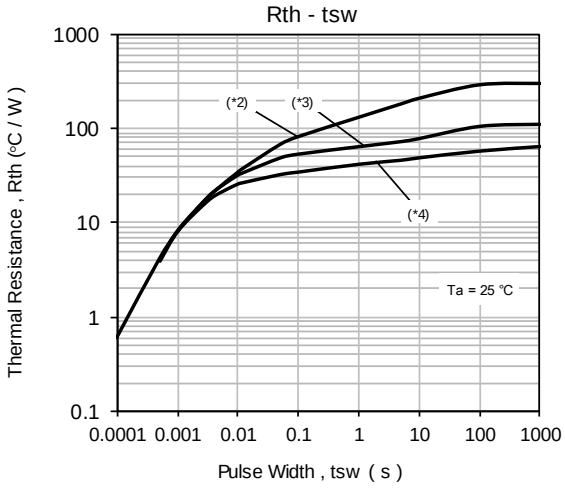
IGS - VGS *1

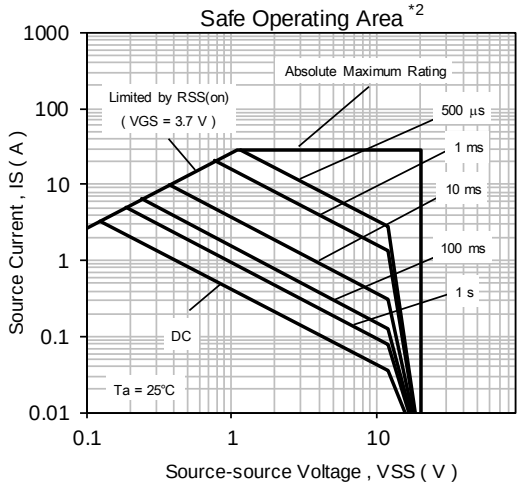


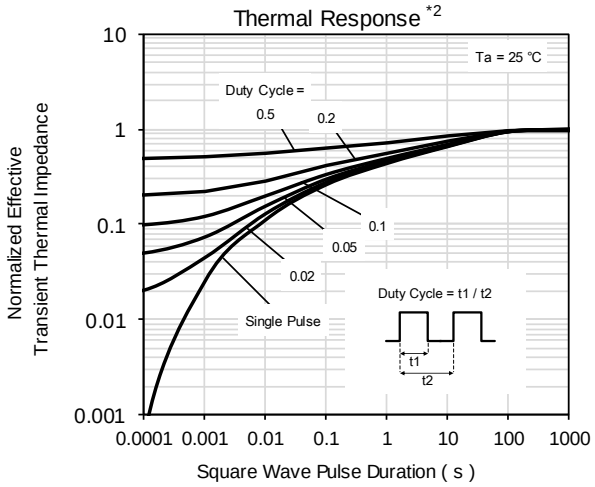
TECHNICAL DATA (Reference)











Note

*1 Pulse measurement.

*2 Mounted on FR4 board (25.4 mm × 25.4 mm × t1.0 mm).
FR4 board partially covered with copper pad
(18 mm^2 area, 36 µm thickness).

*3 Mounted on FR4 board (25.4 mm × 25.4 mm × t1.0 mm).
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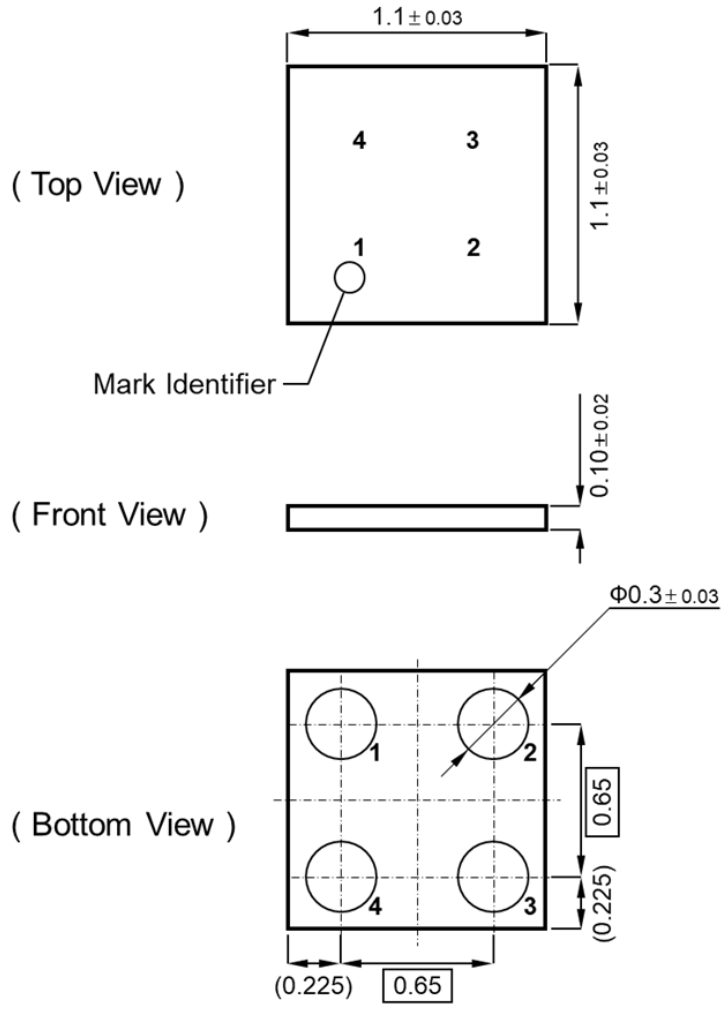
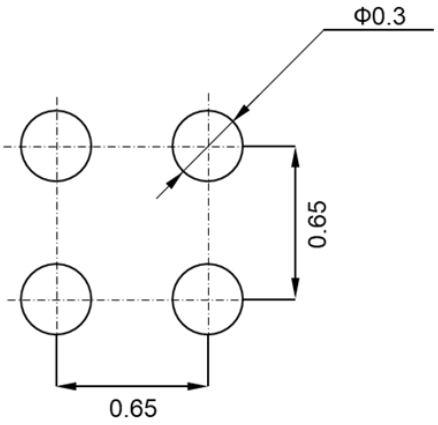
9. OUTLINE

Unit : mm



10. Land & Stencil Pattern (reference)

Unit : mm



11. REVISION HISTORY

Date	Revision	Description
2021.2.5	1.00	1. initially issued.

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